

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE12P09S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages .This device is suitable for use as a load switching application and a wide variety of other applications.

General Features

• $V_{DS} = -12V, I_{D} = -9A$

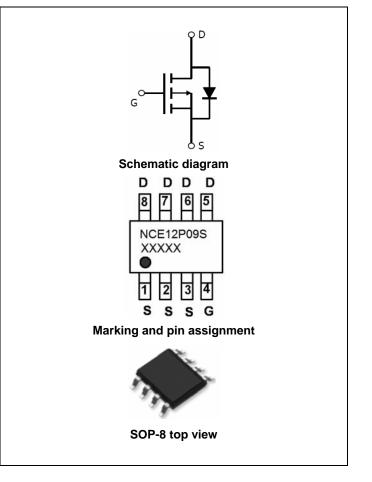
 $R_{DS(ON)}$ < 22m Ω @ V_{GS} =-2.5V

 $R_{DS(ON)}$ < 18m Ω @ V_{GS} =-4.5V

- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge

Application

- PWM applications
- Load switch
- Battery charge in cellular handset



Package marking and ordering information

Device Marking	Device	Device Package	Reel Size	Tape Width	Quantity
NCE12P09S	NCE12P09S	SOP-8	Ø330mm	12mm	4000 units

Absolute maximum ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-12	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current-Continuous	I _D	-9	Α
Drain Current -Pulsed (Note 1)	I _{DM}	-36	Α
Maximum Power Dissipation	P _D	2.5	W
Operating Junction and Storage Temperature Range	T_{J},T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	50	°C/W



Electrical characteristics (T_A=25 $^{\circ}$ unless otherwise noted)

Parameter	Parameter Symbol Condition		Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	V _{(BR) DSS}	V _{GS} =0V I _D =-250μA	-12	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-12V,V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-0.4	-0.7	-1	V
Duain Course On Otata Basistana	Б	V _{GS} =-4.5V, I _D =-9A	-	11.5	18	mΩ
Drain-Source On-State Resistance	$R_{DS(ON)}$	V _{GS} =-2.5V, I _D =-8A	-	14	22	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-9A	20	-	-	S
Dynamic Characteristics (Note4)				•		
Input Capacitance	C _{lss}	\/ 40\/\\ 0\/	-	2700	-	PF
Output Capacitance	C _{oss}	V_{DS} =-10V, V_{GS} =0V, F=1.0MHz	-	680	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0IVIH2	-	590	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	11	-	nS
Turn-on Rise Time	t _r	V_{DD} =-10V, I_{D} =-1A	-	35	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-4.5 V , R_{GEN} =10 Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	\/ - C\/ - OA	-	35	48	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-6V,I _D =-9A, V _{GS} =-4.5V	-	5	-	nC
Gate-Drain Charge	Q_{gd}	v _{GS} =-4.5v	-	10	-	nC
Drain-Source Diode Characteristics	•		•	•		
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-9A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-9	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

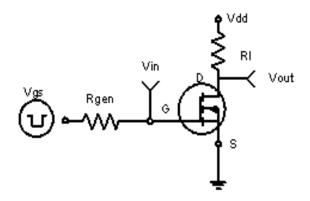


Figure 1:Switching Test Circuit

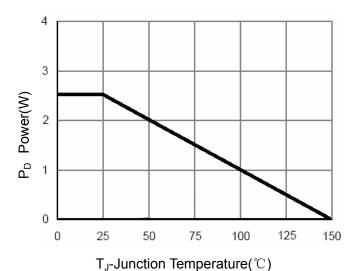


Figure 3 Power Dissipation

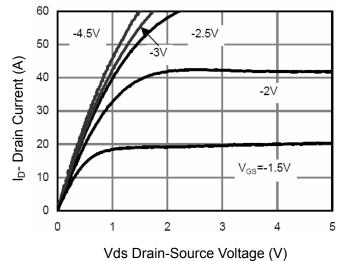


Figure 5 Output Characteristics

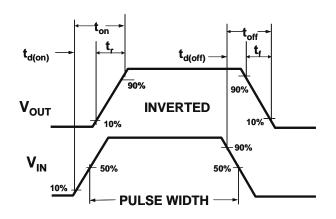


Figure 2:Switching Waveforms

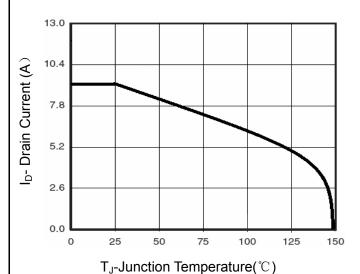


Figure 4 Drain Current

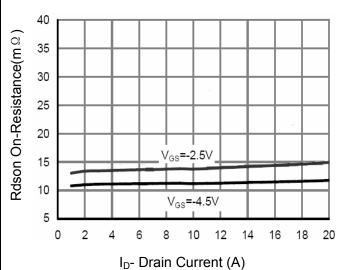
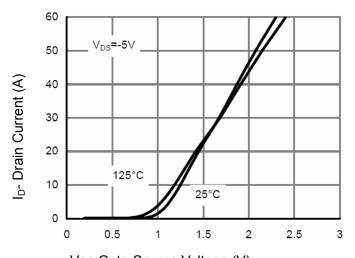


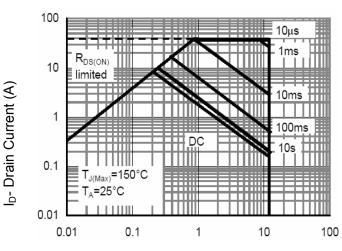
Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)

Figure 7 Transfer Characteristics



Vds Drain-Source Voltage (V)

Figure 9 Safe Operation Area

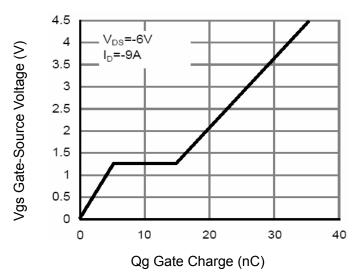
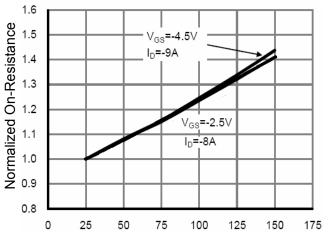
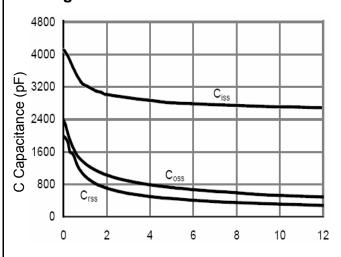


Figure 11 Gate Charge



 T_J -Junction Temperature($^{\circ}$ C)

Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

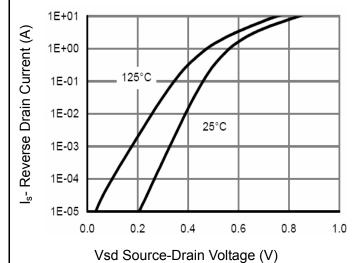


Figure 12 Source- Drain Diode Forward



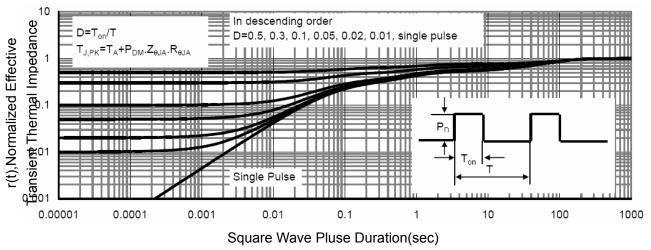
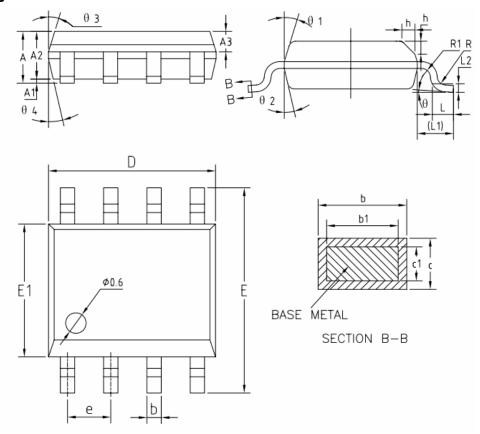


Figure 13 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α	1.35	1.55	1.75	
A1	0.10	0.15	0.25	
A2	1.25	1.40	1.65	
A3	0.50	0.60	0.70	
b	0.38	_	0.51	
b1	0.37	0.42	0.47	
С	0.18	_	0.25	
c1	0.17	0.20	0.23	
D	4.80	4.90	5.00	
E	5.80	6.00	6.20	
E1	3.80	3.90	4.00	
е	1.17	1.27	1.37	
e L	0.45	0.60	0.80	
L1 L2	1.04REF			
L2	0.25BSC			
R	0.07			
R1	0.07	_	ı	
h	0.30	0.40	0.50	
θ	0•	-	8*	
θ 1	15 °	17*	19 °	
θż	11*	13 °	15°	
θ3	15°	17*	19°	
θ 4	11*	13*	15°	



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NCE12P09S

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